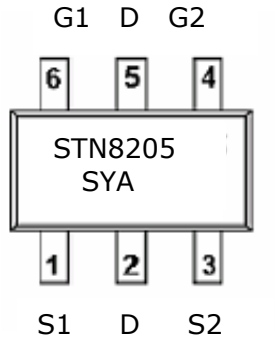
STN8205D

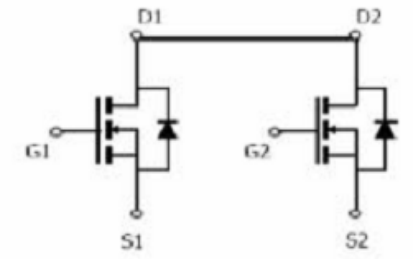
DESCRIPTION

STN8205D is the dual N-Channel enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, such as notebook computer power management and other battery powered circuits, where high-side switching is required.

PIN CONFIGURATION
TSOP-6



S：Subcontractor
Y: Year
A: Week Code



FEATURE

- 20V/4.0A, $R_{DS(ON)}$ = 30m-ohm@V_{GS} =4.5V
- 20V/3.4A, $R_{DS(ON)}$ =42m-ohm@V_{GS} =2.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional low on-resistance and maximum DC current capability
- TSOP-6 package design

ORDERING INFORMATION

Part Number	Package	Part Marking
STN8205DST6RG	TSOP-6	SYA

※ Week Code Code : A ~ Z(1~26) ; a ~ z(27~52)
※ ST8205DST6RG ST6 : TSOP-6; R: Tape Reel ; G: Pb – Free

ABSOULTE MAXIMUM RATINGS (Ta = 25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	+/-20	V
Continuous Drain Current (T_J=150℃)	T_A=25℃	I_D	5.0	A
	T_A=70℃		3.4	
Pulsed Drain Current		I_{DM}	20	A
Continuous Source Current (Diode Conduction)		I_S	2	A
Power Dissipation	T_A=25℃	P_D	1.15	W
	T_A=70℃		0.75	
Operation Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	100	℃/W

ELECTRICAL CHARACTERISTICS (Ta = 25℃ Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS,I_D=250uA	0.6		1.2	V
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=+/-20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V			1	uA
		V_{DS}=20V,V_{GS}=0V T_J=85℃			5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≦5V,V_{GS}=4.5V	5			A
Drain-source On-Resistance	$R_{DS(on)}$	V_{GS}=4.5V,I_D=4.0A		0.025	0.030	Ω
		V_{GS}=2.5V,I_D=3.4A		0.037	0.042	
Forward Transconductance	g_{fs}	V_{DS}=5V,I_D=3.6A		13		S
Diode Forward Voltage	V_{SD}	I_S=1.6A,V_{GS}=0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=10V,V_{GS}=4.5V,V_{DS}=2.8A		10.5		nC
Gate-Source Charge	Q_{gs}			2.0		
Gate-Drain Charge	Q_{gd}			2.5		
Input Capacitance	C_{iss}	V_{DS}=8V,V_{GS}=0V f=1MHz		805		pF
Output Capacitance	C_{oss}			155		
Reverse Transfer Capacitance	C_{rss}			122		
Turn-On Time	$T_{d(on)}$	V_{DD}=10V, RL=10Ω, I_D=4.0A, V_{GEN}=4.5V, RG=6Ω		18		nS
	t_r			5		
Turn-Off Time	$T_{d(off)}$			45		
	t_f			22		